PATENT COOPERATION TREATY

From the INTERNATIONAL SEARCHING AUTHORITY

То:				PCT		
see form PCT/ISA/220				WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43 <i>bis.</i> 1)		
				Date of mailing (day/month/year) see form PCT/ISA/210 (second sheet)		
Applicant's or agent's file reference see form PCT/ISA/220				FOR FURTHER ACTION See paragraph 2 below		
International application No. PCT/JP2004/009077			International filing date (d 22.06.2004	day/month/year)	Priority date (day/month/year) 27.06.2003	
International Pa G03F7/32	atent Clas	sification (IPC) or l	both national classification	and IPC		
Applicant TOKYO OH	KA KOG	SYO CO., LTD.				
1. This op ☑ Box		ontains indication	ons relating to the following	owing items:		
Box Box Box Box	No. II No. III No. IV	Priority Non-establishr Lack of unity o Reasoned stat	nent of opinion with rega f invention ement under Rule 43 <i>bis</i>	s.1(a)(i) with regard to	re step and industrial applicability novelty, inventive step or industrial	
	No. VII	Certain docum Certain defects	tations and explanations ents cited s in the international app ations on the internation	olication	ement	
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submit months whicher	to the IPE from the ver expire	EA a written repleted date of mailing estater.	y together, where appro of Form PCT/ISA/220 or	priate, with amendme	PEA, the applicant is invited to nts, before the expiration of three of 22 months from the priority date,	
	For further options, see Form PCT/ISA/220. For further details, see notes to Form PCT/ISA/220.					

Name and mailing address of the ISA:

Authorized Officer

<u>)</u>

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10/561802

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No. PCT/JP2004/009077

Box No. I Basis of the opinion
 With regard to the language, this opinion has been established on the basis of the international application in the language in which it was filed, unless otherwise indicated under this item.
This opinion has been established on the basis of a translation from the original language into the following language , which is the language of a translation furnished for the purposes of international search (under Rules 12.3 and 23.1(b)).
With regard to any nucleotide and/or amino acid sequence disclosed in the international application and necessary to the claimed invention, this opinion has been established on the basis of:
a. type of material:
☐ a sequence listing
☐ table(s) related to the sequence listing
b. format of material:
☐ in written format
in computer readable form
c. time of filing/furnishing:
contained in the international application as filed.
filed together with the international application in computer readable form.
furnished subsequently to this Authority for the purposes of search.
3. In addition, in the case that more than one version or copy of a sequence listing and/or table relating thereto has been filed or furnished, the required statements that the information in the subsequent or additional copies is identical to that in the application as filed or does not go beyond the application as filed, as appropriate, were furnished.
4. Additional comments:

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WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (SEPARATE SHEET)

International application No.

PCT/JP2004/009077

IAP20 Res'4757770 22 DEC 2005

Re Item V.

Reference is made to the following documents:

D1: US5985525 D2: EP272686 D3: EP323836

To novelty:

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None of the cited prior art documents describes a combination of an quaternary ammonium alkaline agent in combination with a sodium salt of a substituted diphenyl ether sulfonate as surfactant in a developer composition for (photo)resists. Novelty in the sense of Art. 33(2) PCT is acknowledged for the subject-matter of claims 1-3.

To inventive step

The present application does not meet the criteria of Article 33(1) PCT, because the subject-matter of claims 1-3 does not involve an inventive step in the sense of Article 33(3) PCT.

The closest prior is D1, which is believed to be similar to the document cited by the applicant in the description on P.2. It describes a developing composition for resists comprising a quaternary ammonium hydroxide as alkaline agent in combination with a surfactant based on ammonium salts of a substituted diphenylether sulfonic acid.

The present application differs from this prior art in that a metal salt, preferably sodium, potassium or calcium is used as cation instead of ammonium in the surfactant. In the examples it is shown that the dissolution time required for removing a resist is shortened when comparing with the surfactant of D1. According to the description, the improved wetting will have a positive impact on selectivity and thereby yield better profiles and improve the resolution.

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (SEPARATE SHEET)

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International application No.

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The problem which had to be solved according to the description can be defined as overcoming the shortcomings of the surfactants used in D1, which have less than optimum properties as far as wettability and enhancement of dissolution are concerned.

It should be noted that anionic surfactants with quaternary ammonium counter-ions have been chosen in the production of semiconductors because of the sensitivity of the substrates to metal impurities. Traditional surfactants for developing compositions in fields such as printing plates or printed circuit boards are however mostly sodium salts of a variety of anionic surfactants, including sodium salts of substituted diphenylether sulfonates. The introduction of metal-free compositions for semiconductors has never been based on performance considerations as far as the development itself is concerned, but has been imposed by the nature of the underlying substrate, as acknowledged by the applicant in the description. D1 clearly mentions (column 1, bottom) that the use of these ammonium surfactants is not the ideal solution as far as the development properties are concerned. And the examples of the application show that the ammonium salt even has a detrimental effect on the dissolution time when comparing with a composition free of surfactant (comp. Ex.2).

The person skilled in the art who is aware of the evolution of the general technology would, when confronted with a problem in a process where metal contaminations are of no major concern, consider the use of compositions which have already shown good performance in applications where naphtoquinone diazide based resists coated on a metal are developed. D3 (as well as D2) clearly mention that the choice of the alkaline agent includes metal-free as well as metal containing compounds, while sodium alkyl diphenyl ether disulfonates are among the recommended surfactants. To adapt these general recommendations to a particular application as defined by the present claims is well within the reach of the person skilled in the art, without requiring any inventive activity.